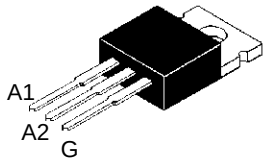
SGS-THOMSON MICROELECTRONICS

T0805xH
T0809xH

SENSITIVE GATE TRIACS

FEATURES

- $I_{T(RMS)}$ = 8A
- V_{DRM} = 400V to 800V
- $I_{GT} \leq$ 5mA to $\leq$ 10mA



TO220
non-insulated
(Plastic)

DESCRIPTION

The T08xxxH series of triacs uses a high performance MESA GLASS technology. These parts are intended for general purpose applications where gate high sensitivity is required.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	Tc= 95 °C	8	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	tp = 8.3 ms	73	A
		tp = 10 ms	70	
I^2t	I^2t Value for fusing	tp = 10 ms	24	A^2s
dI/dt	Critical rate of rise of on-state current I_G = 50 mA di_G/dt = 0.1 A/µs.	Repetitive F = 50 Hz	10	A/µs
		Non Repetitive	50	
T_{stg} T_j	Storage and operating junction temperature range		- 40, + 150 - 40, + 125	°C
Tl	Maximum lead temperature for soldering during 10s at 4.5mm from case		260	°C

Symbol	Parameter	Voltage				Unit
		D	M	S	N	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage T_j = 125°C	400	600	700	800	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	60	°C/W
Rth(j-c)	Junction to case for D.C	4	°C/W
Rth(j-c)	Junction to case for A.C 360° conduction angle (F=50Hz)	3	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G\ (AV)}$= 1 W P_{GM} = 10 W (tp = 20 µs) I_{GM} = 4 A (tp = 20 µs)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Sensitivity		Unit
					05	09	
I_{GT}	V_D=12V (DC) R_L=33Ω	Tj= 25°C	I-II-III-IV	MAX	5	10	mA
V_{GT}	V_D=12V (DC) R_L=33Ω	Tj= 25°C	I-II-III-IV	MAX	1.5		V
V_{GD}	V_D=V_{DRM} R_L=3.3kΩ	Tj= 125°C	I-II-III-IV	MIN	0.2		V
tgt	V_D=V_{DRM} I_G = 40mA I_T = 11A dI_G/dt = 0.5A/µs	Tj= 25°C	I-II-III-IV	TYP	2		µs
I_H *	I_T= 50mA Gate open	Tj= 25°C		MAX	5	10	mA
I_L	I_G= 1.2 I_{GT}	Tj= 25°C	I-III-IV	TYP	5	10	mA
			II	TYP	10	20	
V_{TM} *	ITM= 11A tp= 380µs	Tj= 25°C		MAX	1.65		V
I_{DRM} I_{RRM}	V_D = V_{DRM} V_R = V_{RRM}	Tj= 25°C		MAX	5		µA
		Tj= 110°C		MAX	2		mA
dV/dt *	VD=67%V_{DRM} Gate open	Tj= 110°C		MIN		20	V/µs
				TYP	10		
(dV/dt)c *	(dI/dt)c = 3.5 A/ms	Tj= 110°C		TYP	1	2	V/µs

* For either polarity of electrode A_2 voltage with reference to electrode A_1

ORDERING INFORMATION

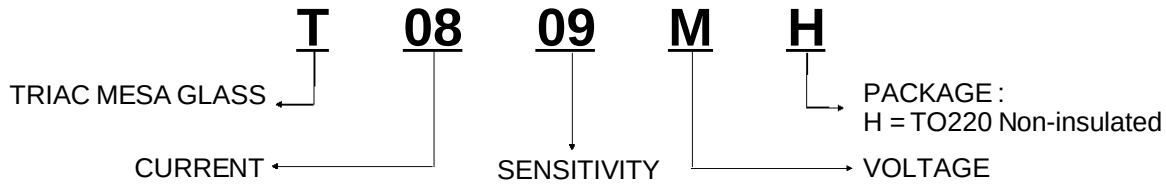


Fig.1 : Maximum RMS power dissipation versus RMS on-state current.

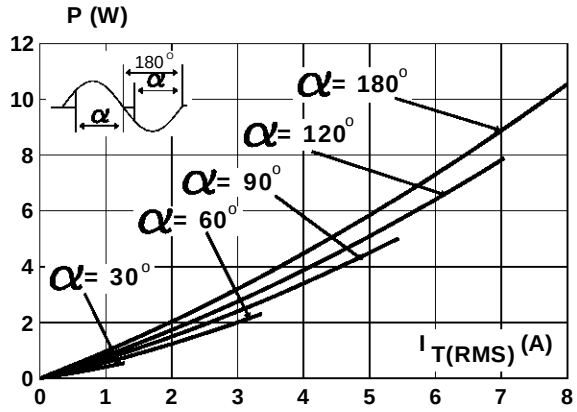


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperature (Tamb and Tcase) for different thermal resistances heatsink + contact.

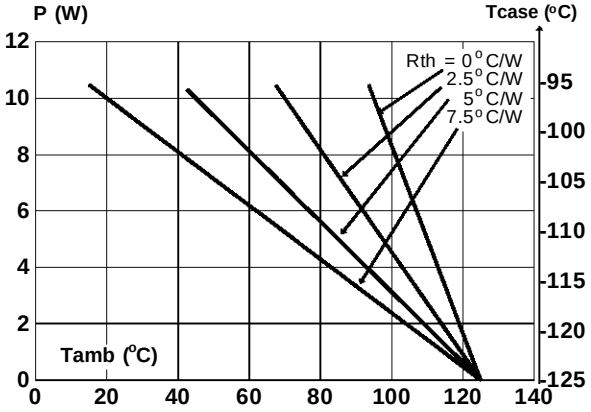


Fig.3 : RMS on-state current versus case temperature.

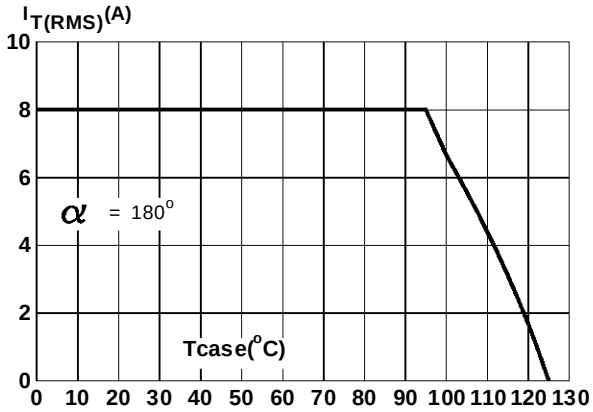


Fig.4 : Relative variation of thermal impedance versus pulse duration.

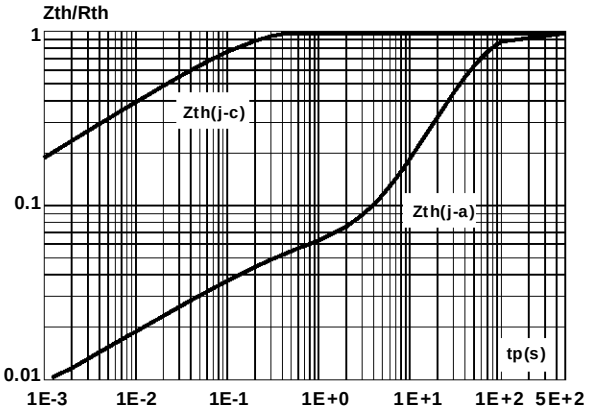


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

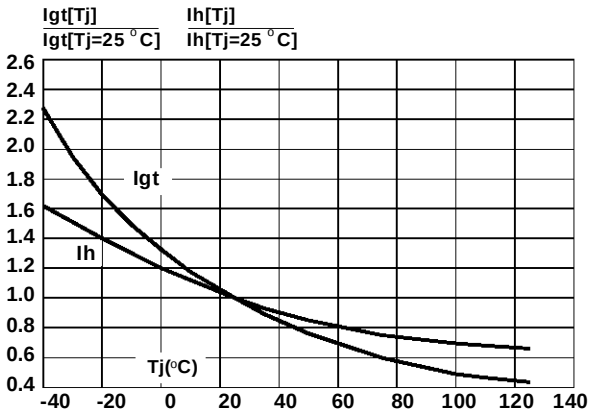


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

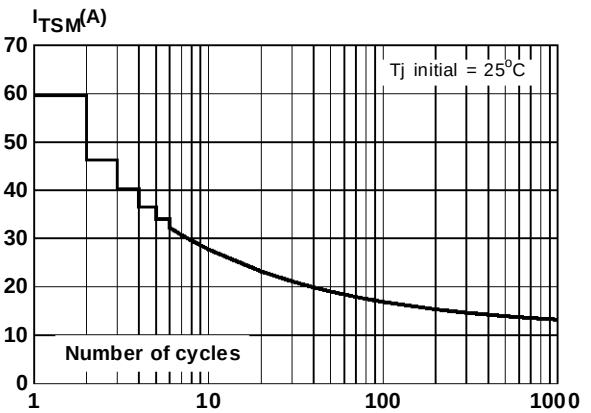


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10ms$, and corresponding value of I^2t.

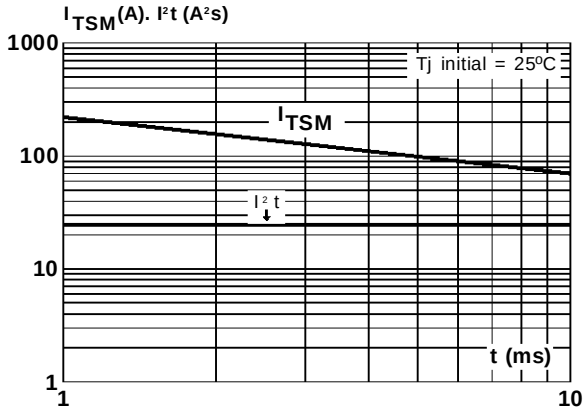
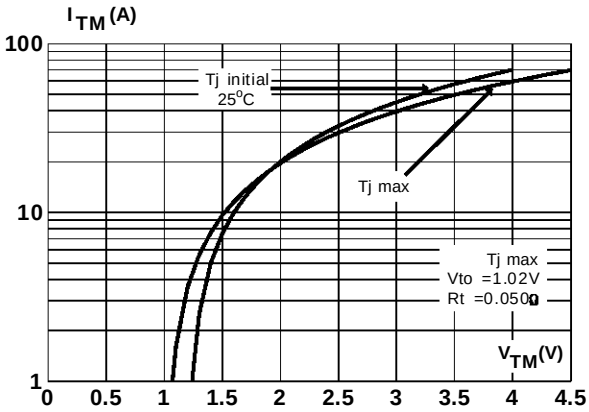
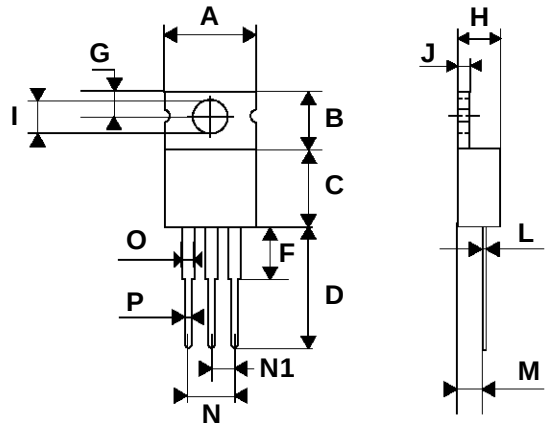


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA
TO220 Non-insulated (Plastic)



REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A			10.3			0.406
B		6.3	6.5	0.248	0.256	
C			9.1			0.358
D		12.7			0.500	
F			4.2			0.165
G			3.0			0.118
H		4.5	4.7		0.177	0.185
I		3.53	3.66		0.139	0.144
J		1.2	1.3		0.047	0.051
L			0.9			0.035
M	2.7			0.106		
N			5.3			0.209
N1	2.54			0.100		
O		1.2	1.4		0.047	0.055
P			1.15			0.045

Marking : type number
Weight : 1.8 g